



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
-30V	5Ω @ V _{GS} = -4.5V	
	6Ω @ V _{GS} = -2.5V	-0.2A
	7Ω @ V _{GS} = -1.8V	-0.2A
	10Ω @ V _{GS} = -1.5V	

Description and Applications

This MOSFET has been designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch



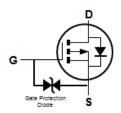


Features and Benefits

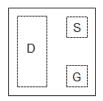
- Low Package Profile, 0.42mm Maximum Package Height
- 0.62mm x 0.62mm Package Footprint
- Low On-Resistance
- Very Low Gate Threshold Voltage, -1.0V Max
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: X2-DFN0606-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208@4
- Weight: 0.001 grams (Approximate)



Equivalent Circuit



Top View Package Pin Configuration

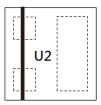
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP32D9UFZ-7B	X2-DFN0606-3	10k/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



Top View Bar Denotes Gate and Source Side

U2 = Product Type Marking Code



Maximum Ratings $(@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	±10	V
Continuous Drain Current (Note 5) V _{GS} = -4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	-200 -100	mA
Pulsed Drain Current (Note 6)			I _{DM}	-700	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	Steady State	P_{D}	390	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	322	°C/W
Operating and Storage Temperature Range	$T_{J_i}T_{STG}$	-55 to +150	°C	

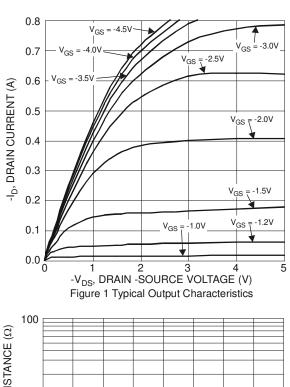
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

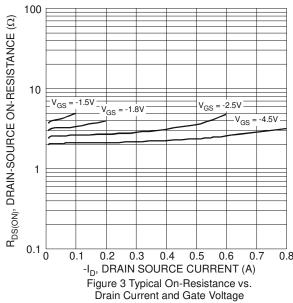
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)				ı	I		
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current $@T_C = +25^{\circ}C$	I _{DSS}	_	_	-100	nA	$V_{DS} = -24V, V_{GS} = 0V$	
Gate-Source Leakage		_	_	±10	μΑ	$V_{GS} = \pm 10V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	-0.4	_	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
			_	5		$V_{GS} = -4.5V, I_D = -100mA$	
		1	_	6		$V_{GS} = -2.5V, I_D = -50mA$	
Static Drain-Source On-Resistance	R _{DS(ON)}		_	7	Ω	$V_{GS} = -1.8V, I_D = -20mA$	
			_	10		$V_{GS} = -1.5V, I_D = -10mA$	
			6	_		$V_{GS} = -1.2V, I_D = -1mA$	
Diode Forward Voltage			-0.75	-1.0	V	$V_{GS} = 0V, I_{S} = -10mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance			22.5	_	pF	151/1/1	
Output Capacitance	Coss		2.9	_	pF	$V_{DS} = -15V, V_{GS} = 0V,$ -f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	2.1	_	pF	1 = 1.0WH12	
Total Gate Charge	Qg	_	0.35	_	nC		
Gate-Source Charge	Qgs	_	0.06	_	nC	$V_{GS} = -4.5V, V_{DS} = -5V,$ $V_{DS} = -200mA$	
Gate-Drain Charge	Q_{gd}	_	0.09	_	nC	ID = -200IIIA	
Turn-On Delay Time	t _{D(ON)}	_	3.1	_	ns		
Turn-On Rise Time	t _R	-	2.3	_	ns	$V_{DD} = -10V, V_{GS} = -4.5V,$	
Turn-Off Delay Time		_	19.9	_	ns	$R_G = 6\Omega$, $I_D = -200$ mA	
Turn-Off Fall Time			10.5	_	ns		

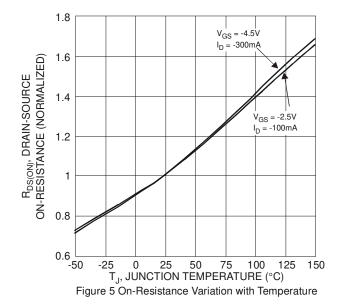
Notes:

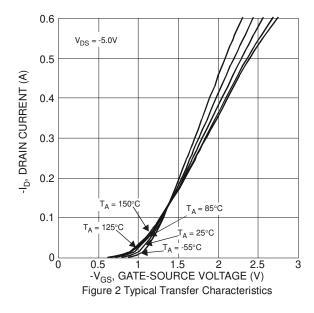
- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 6. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.

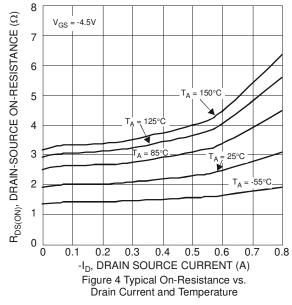












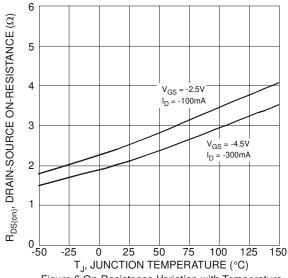


Figure 6 On-Resistance Variation with Temperature

DMP32D9UFZ



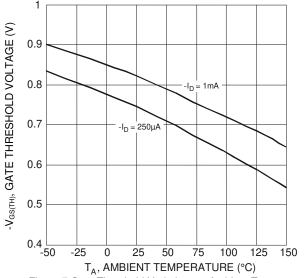
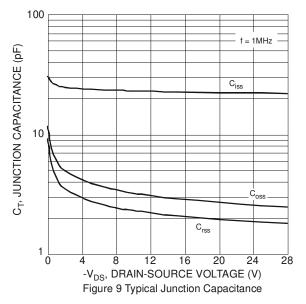
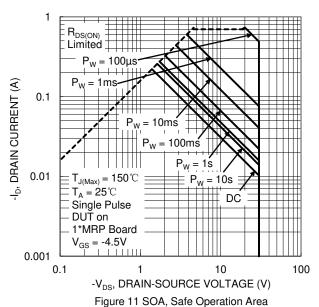
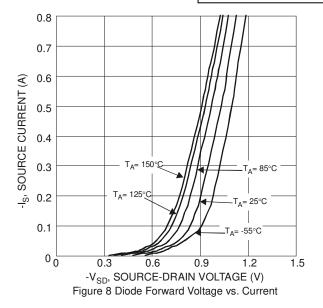
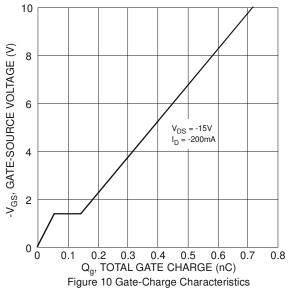


Figure 7 Gate Threshold Variation vs. Ambient Temperature

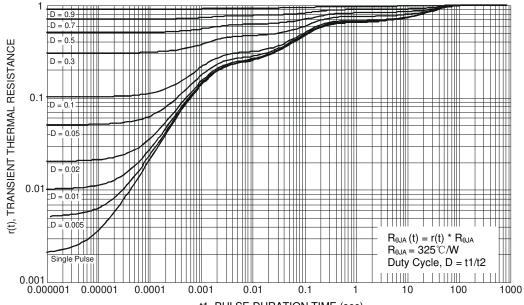












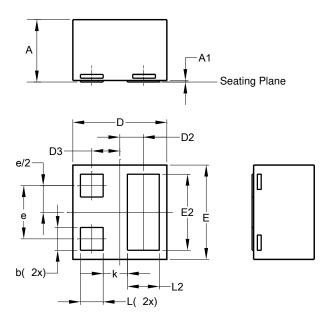
t1, PULSE DURATION TIME (sec) Figure 12 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN0606-3

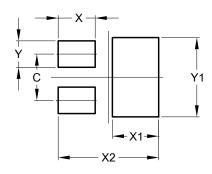


X2-DFN0606-3					
Dim	Min	Тур			
Α	0.36	0.42	0.39		
A 1	0	0.05	0.02		
b	0.10	0.20	0.15		
D	0.57	0.67	0.62		
D2	0.155 BSC				
D3	0.185 BSC				
Е	0.57 0.67 0.		0.62		
E2	0.40	0.60	0.50		
е	0.35 BSC				
k	0.16 REF				
L	0.09	0.21	0.15		
L2	0.11	0.31	0.21		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN0606-3



Dimensions	Value (in mm)		
С	0.350		
Х	0.280		
X1	0.350		
X2	0.760		
Υ	0.200		
Y1	0.600		



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